

*ABSTRACT AMENDMENT*

Replace the Abstract with:

A gate oxide film is formed on a substrate. A polysilicon film is formed on the gate oxide film. A ruthenium film is formed as a mask material on the polysilicon film. A resist pattern is formed on the ruthenium film. After the ruthenium film is patterned using the resist pattern as a mask, ~~a~~ the patterned ruthenium film is shrunk. After the polysilicon film is patterned using ~~a shrunk~~ the shrunken ruthenium film, the ~~shrunk~~ shrunken ruthenium film is removed.